

What is claimed is;

- Sub 4
1. A semiconductor device comprising;
a semiconductor substrate formed reference lines at a circuit forming surface with a pad electrode provided at the periphery thereof, in correspondence to the positions of at least three corners of a semiconductor element to serve as reference marks indicating positions at which semiconductor elements of varying sizes are to be mounted,
a semiconductor element mounted at said circuit forming surface of said semiconductor substrate,
resin that seals a specific area on said semiconductor substrate containing said semiconductor element.
 2. A semiconductor device according to claim 1, wherein;
said reference lines are formed through silk-screen printing.
 3. A semiconductor device according to claim 1, wherein;
said reference lines are constituted of an adhesive.
 4. A semiconductor device according to claim 1, wherein;
said reference lines are formed by removing a metal film at an area over which said reference lines are to be formed concurrently with a step in which said pad electrode is formed by removing said metal film on said circuit forming surface at said semiconductor substrate is in progress.
 5. A semiconductor device according to claim 1, wherein;
said reference lines are formed by removing a metal film outside an area over which said reference lines are to be formed concurrently with a step in which said pad electrode is formed by removing said

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metal film on said circuit forming surface at said semiconductor substrate is in progress.

6. A semiconductor device according to claim 5, wherein;
said reference lines are formed so as to extend to the outside of the resin-sealed area.
7. A semiconductor device according to claim 5, wherein;
ribs are formed at said reference lines in correspondence to the positions of corners of semiconductor elements of at least two sizes.
8. A semiconductor device according to claim 5, wherein;
frame portions indicating the outer parameters of semiconductor elements of at least two sizes are formed at said reference lines.
9. A semiconductor device according to claim 5, wherein;
a second metal layer containing at least Au is formed at said reference lines.
10. A semiconductor device comprising;
a semiconductor substrate formed a cross mark at a circuit forming surface with a pad electrode provided at the periphery thereof, in correspondence to the positions of four corners of a semiconductor element to serve as reference marks indicating positions at which semiconductor elements of varying sizes are to be mounted,
a semiconductor element mounted at said circuit forming surface of said semiconductor substrate,
resin that seals a specific area on said semiconductor substrate containing said semiconductor element.

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11. A semiconductor device according to claim 10, wherein;
said reference lines are formed through silk-screen printing.
12. A semiconductor device according to claim 10, wherein;
said reference lines are constituted of an adhesive.
13. A semiconductor device according to claim 10, wherein;
said reference lines are formed by removing a metal film at an area over which said reference lines are to be formed concurrently with a step in which said pad electrode is formed by removing said metal film on said circuit forming surface at said semiconductor substrate is in progress.
14. A semiconductor device according to claim 10, wherein;
said reference lines are formed by removing a metal film outside an area over which said reference lines are to be formed concurrently with a step in which said pad electrode is formed by removing said metal film on said circuit forming surface at said semiconductor substrate is in progress.
15. A semiconductor device according to claim 14, wherein;
said reference lines are formed so as to extend to the outside of the resin-sealed area.
16. A semiconductor device according to claim 14, wherein;
ribs are formed at said reference lines in correspondence to the positions of corners of semiconductor elements of at least two sizes.
17. A semiconductor device according to claim 14, wherein;

FOOTNOTES

frame portions indicating the outer parameters of semiconductor elements of at least two sizes are formed at said reference lines.

18. A semiconductor device according to claim 14, wherein;
a second metal layer containing at least Au is formed at said reference lines.

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